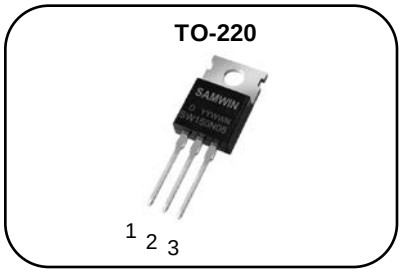
N-channel Enhancement mode TO-220 MOSFET

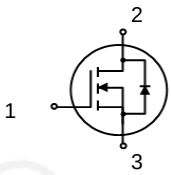
Features

- High ruggedness
- $R_{DS(ON)}$ (Typ 5.5mΩ)@V_{GS}=10V
- Gate Charge (Typ 117nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application: DC-DC，E-Bike



1. Gate 2. Drain 3. Source

BV_{DSS} : 80V
I_D : 150A
$R_{DS(ON)}$: 5.5mΩ



General Description

This power MOSFET is produced with advanced technology of SAMWIN.
This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

LEAD-FREE RoHS

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 150N08D	SW150N08D	TO-220	TUBE

Absolute maximum ratings

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		80	V
I_D	Continuous Drain Current (@T_C=25°C)		150*	A
	Continuous Drain Current (@T_C=100°C)		94.5*	A
I_{DM}	Drain current pulsed	(note 1)	600	A
V_{GS}	Gate to Source Voltage		±20	V
E_{AS}	Single pulsed Avalanche Energy	(note 2)	1360	mJ
E_{AR}	Repetitive Avalanche Energy	(note 1)	100	mJ
dv/dt	Peak diode Recovery dv/dt	(note 3)	5	V/ns
P_D	Total power dissipation (@T_C=25°C)		312.5	W
	Derating Factor above 25°C		2.5	W/°C
T_{STG}, T_J	Operating Junction Temperature & Storage Temperature		-55 ~ + 150	°C
T_L	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.		300	°C

*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value	Unit
R_{thjc}	Thermal resistance, Junction to case	0.4	°C/W
R_{thcs}	Thermal resistance, Case to Sink	0.5	°C/W
R_{thja}	Thermal resistance, Junction to ambient	57.4	°C/W

Electrical characteristic (T_C = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	V_{GS}=0V, I_D=250uA	80			V
ΔBV_{DSS} / ΔT_J	Breakdown voltage temperature coefficient	I_D=250uA, referenced to 25°C		0.06		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=150V, V_{GS}=0V			1	uA
		V_{DS}=120V, T_C=125°C			50	uA
I_{GSS}	Gate to source leakage current, forward	V_{GS}=20V, V_{DS}=0V			100	nA
	Gate to source leakage current, reverse	V_{GS}=-20V, V_{DS}=0V			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=250uA	2.0		4.0	V
$R_{DS(ON)}$	Drain to source on state resistance	V_{GS}=10V, I_D =80A		5.5	6	mΩ
Gfs	Forward Transconductance	V_{DS} = 10V, I_D = 40A		83		S
Dynamic characteristics						
C_{iss}	Input capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz		6789		pF
C_{oss}	Output capacitance			772		
C_{rss}	Reverse transfer capacitance			519		
$t_{d(on)}$	Turn on delay time	V_{DS}=40V, I_D=70A, R_G=25Ω (note 4，5)		79		nS
tr	Rising time			143		
$t_{d(off)}$	Turn off delay time			225		
t_f	Fall time			159		
Q_g	Total gate charge	V_{DS}=64V, V_{GS}=10V, I_D=70A (note 4，5)		117		nC
Q_{gs}	Gate-source charge			27		
Q_{gd}	Gate-drain charge			50		

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			150	A
I_{SM}	Pulsed source current				600	A
V_{SD}	Diode forward voltage drop.	I_S=70A, V_{GS}=0V			1.5	V
T_{rr}	Reverse recovery time	I_S=70A, V_{GS}=0V, dI_F/dt=100A/us		45		nS
Q_{rr}	Breakdown voltage charge			88		nC

※. Notes

1. Repeatitive rating : pulse width limited by junction temperature.
2. L =1.7mH, I_{AS} = 70A, V_{DD} = 50V, R_G=25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 70A, di/dt = 100A/us, V_{DD} ≤ BV_{DSS}, Staring T_J =25°C
4. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%
5. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

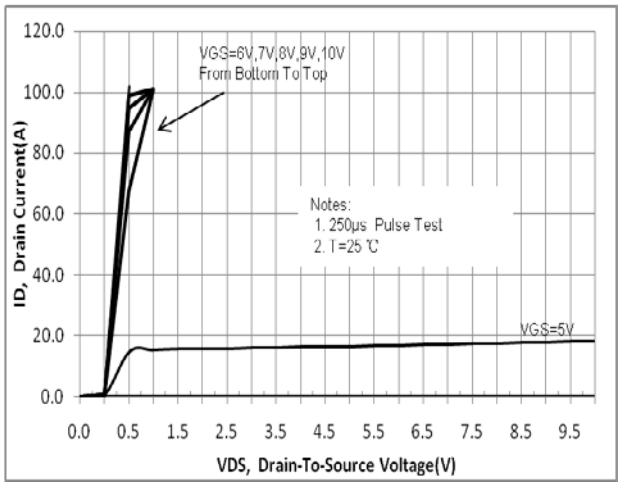


Fig. 2. On-resistance variation vs. drain current and gate voltage

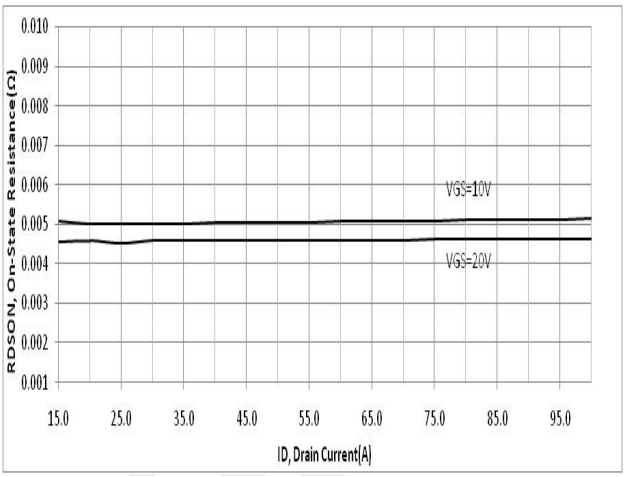


Fig. 3. Gate charge characteristics

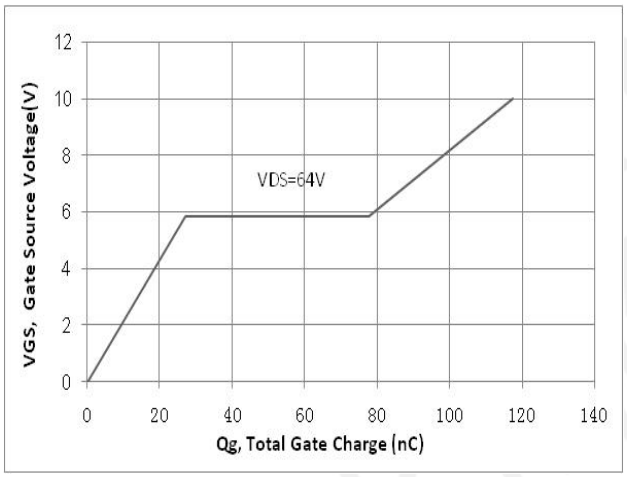


Fig. 4. On state current vs. diode forward voltage

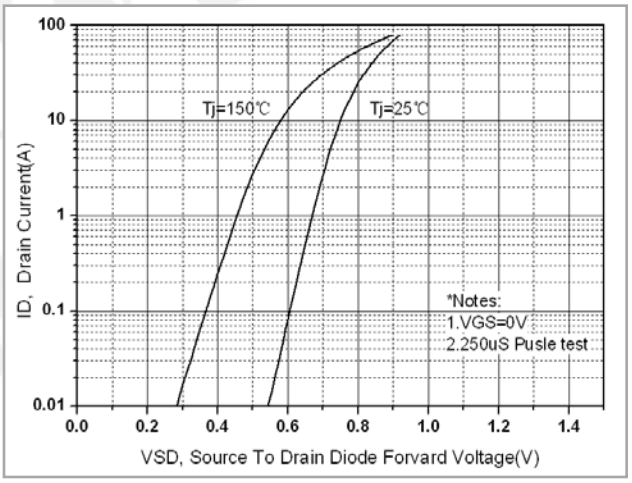


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

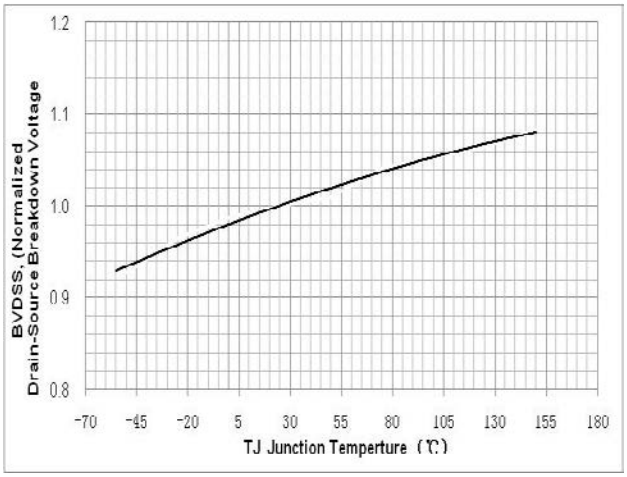


Fig. 6. On resistance variation vs. junction temperature

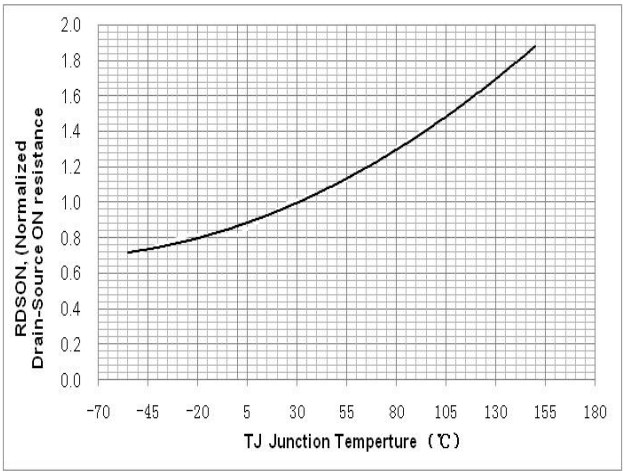


Fig. 7. Maximum safe operating area

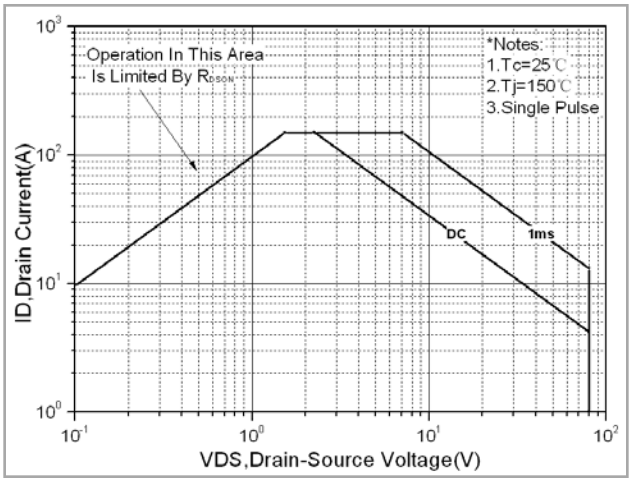


Fig. 8. Transient thermal response curve

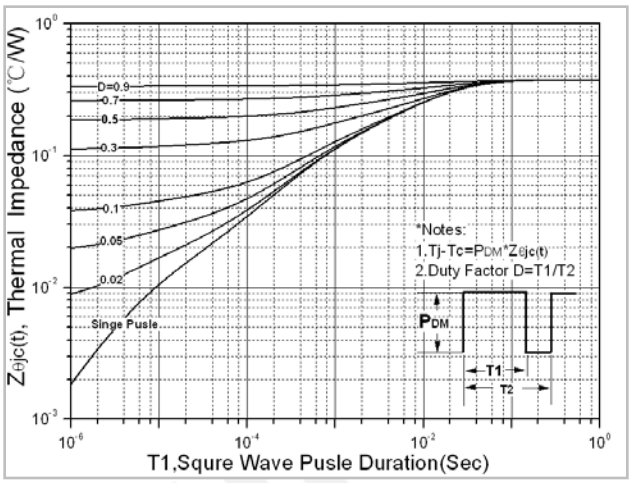


Fig. 9. Capacitance Characteristics

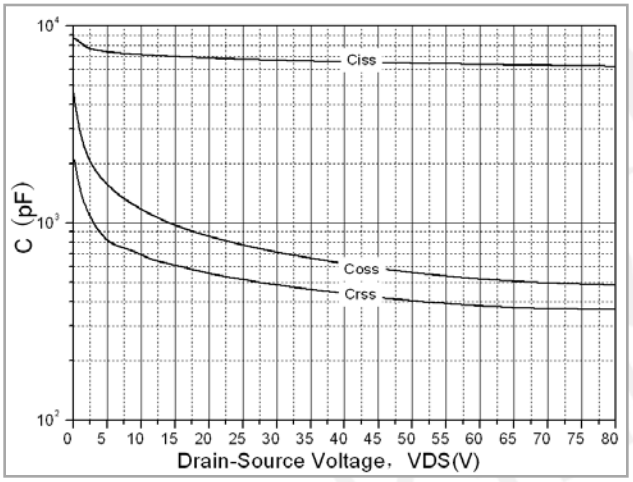
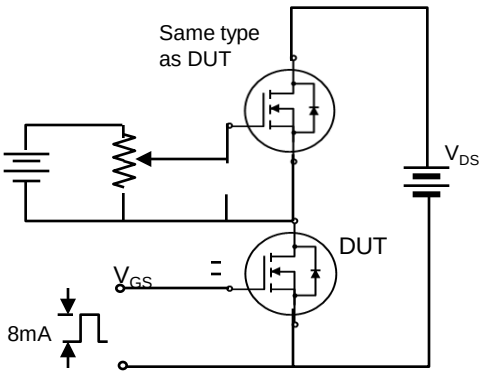


Fig. 10. Gate charge test circuit & waveform



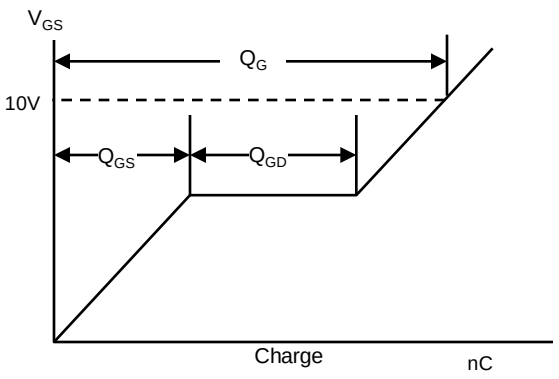


Fig. 11. Switching time test circuit & waveform

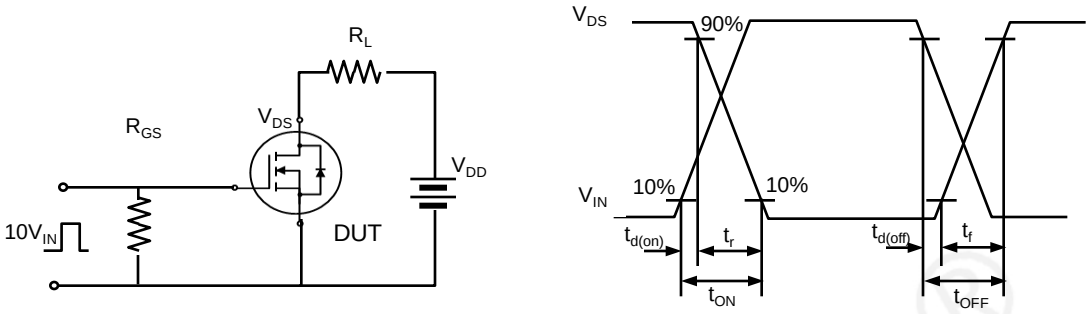


Fig. 12. Unclamped Inductive switching test circuit & waveform

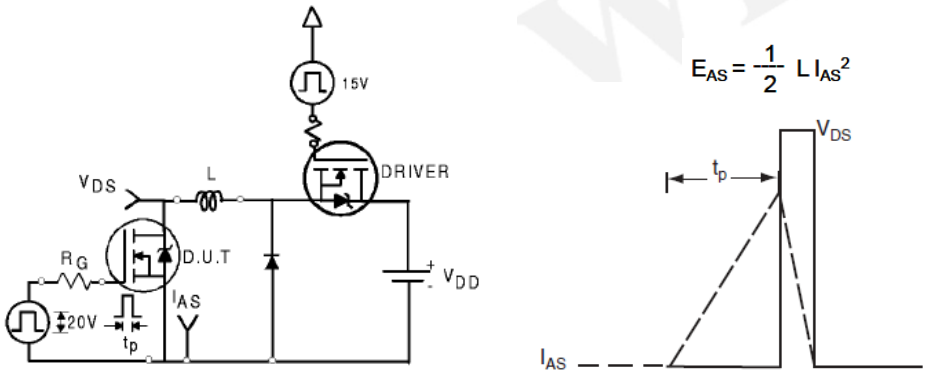
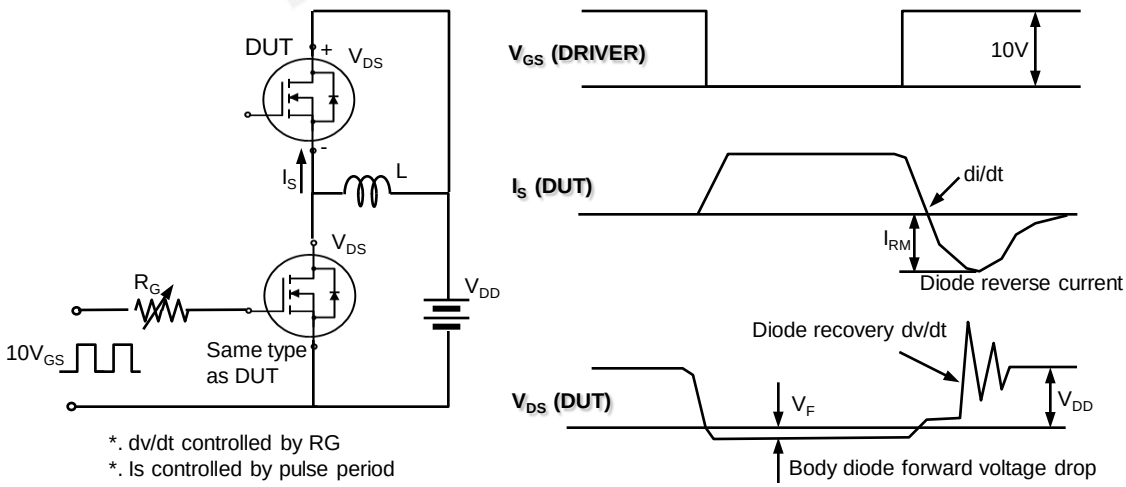


Fig. 13. Peak diode recovery dv/dt test circuit & waveform



*. dv/dt controlled by RG
*. Is controlled by pulse period

DISCLAIRATION:

* All the data&curve within this document was tested in XI'AN SEMIPOWER TESTING&APPLICATION CENTER.
* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
* Qualification Standards can also be found on the Web site (**http://www.semipower.com.cn**)
* Any advice, please send your proposal to **samwin@samwinsemi.com**